Pch -30V -12A Middle Power MOSFET

V _{DSS}	-30V
R _{DS(on)} (Max.)	8.0mΩ
I _D	±12A
P _D	2W

Features

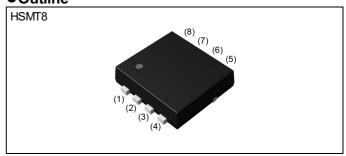
- 1) Low on resistance.
- 2) High Power small mold Package (HSMT8).
- 3) Pb-free lead plating; RoHS compliant.
- 4) Halogen Free.

Application

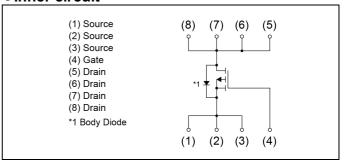
Switching

● Absolute maximum ratings (T _a = 25°C)						
Parameter	Symbol	Value	Unit			
Drain - Source voltage	V _{DSS}	-30	V			
Continuous drain current	I _D	±12	Α			
Pulsed drain current	I _{D,pulse} *2	±48	Α			
Gate - Source voltage	V_{GSS}	±20	V			
Power dissipation	P _D *1	2	W			
Junction temperature	T _j	150	°C			
Range of storage temperature	T _{stg}	-55 to +150	°C			

Outline



●Inner circuit



Packaging specifications

	Packing	Embossed Tape
Туре	Reel size (mm)	330
	Tape width (mm)	12
	Basic ordering unit (pcs)	3000
	Taping code	ТВ
	Marking	E120AT

●Thermal resistance

Devenueten	Symbol	Values			Lloit
Parameter	Symbol	Min.	Тур.	Max.	Unit
Thermal resistance, junction - ambient	R _{thJA} *1	-	62.5	-	°C/W

● Electrical characteristics (T_a = 25°C)

Parameter	Sumb of	Conditions	Values			Unit	
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic	
Drain - Source breakdown voltage	V _{(BR)DSS}	$V_{GS} = 0V$, $I_D = -1mA$	-30	-	-	V	
Breakdown voltage	$\Delta V_{(BR)DSS}$	I _D = -1mA	_	-22	-	mV/°C	
temperature coefficient	ΔT_j	referenced to 25°C	_	-22	_	11107 C	
Zero gate voltage drain current	I _{DSS}	$V_{DS} = -30V, V_{GS} = 0V$	ı	1	-1	μA	
Gate - Source leakage current	I _{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$	ı	1	±100	nA	
Gate threshold voltage	V _{GS(th)}	$V_{DS} = -10V, I_{D} = -1mA$	-1.0	-	-2.5	V	
Gate threshold voltage	$\Delta V_{GS(th)}$	I _D = -1mA		2.0		m\//°C	
temperature coefficient	ΔT_j	referenced to 25°C - 2.9		2.9	-	mV/°C	
Static drain - source	D *3	V _{GS} = -10V, I _D = -12A	-	6.1	8.0	C	
on - state resistance	$R_{DS(on)}^{*3}$	V _{GS} = -4.5V, I _D = -12A	-	8.7	11.3	mΩ	
Forward Transfer Admittance	Y _{fs} *3	V _{DS} = -5V, I _D = -12A	15	-	-	S	

^{*1} MOUNTED ON 40mm×40mm Cu BOARD

^{*2} Pw \leq 10 μ s, Duty cycle \leq 1%

^{*3} Pulsed

●Electrical characteristics (T_a = 25°C)

Doromotor	Symbol	Conditions		Unit		
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Input capacitance	C _{iss}	V _{GS} = 0V	-	3200	-	
Output capacitance	C _{oss}	V _{DS} = -15V	-	550	-	pF
Reverse transfer capacitance	C _{rss}	f = 1MHz	-	410	-	
Turn - on delay time	t _{d(on)} *3	V _{DD} ≈ -15V,V _{GS} = -10V	-	20	-	
Rise time	t _r *3	I _D = -6A	-	30	-	
Turn - off delay time	t _{d(off)} *3	R _L ~ 2.5Ω	-	140	-	ns
Fall time	t _f *3	R _G = 10Ω	-	95	-	

• Gate charge characteristics $(T_a = 25^{\circ}C)$

Darameter	Symbol	Conditions		Values			1.1:4
Parameter	Symbol			Min.	Тур.	Max.	Unit
Total gate above	Q_g^{*3}	V _{DD} ≃ -15V	V _{GS} = -10V	-	62	-	
Total gate charge				-	33	-	
Gate - Source charge	Q _{gs} *3	I _D = -12A	V _{GS} = -4.5V	-	9	-	nC
Gate - Drain charge	Q _{gd} *3			-	12	-	

● Body diode electrical characteristics (Source-Drain) (T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
	Symbol	ol Conditions -		Тур.	Max.	Offic
Body diode continuous forward current	I _S	⊤ _a = 25°C	-	1	-1.67	А
Body diode pulse current	I _{SP} *2	1 _a - 25 C	-	-	-48	А
Forward voltage	V _{SD} *3	$V_{GS} = 0V, I_{S} = -1.67A$	-	ı	-1.2	V

Fig.1 Power Dissipation Derating Curve

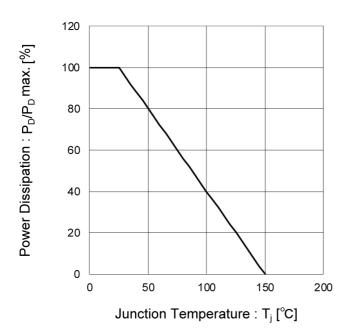
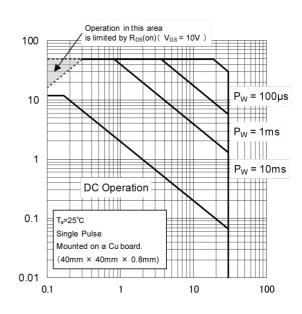


Fig.2 Maximum Safe Operating Area



Drain Current: -l_D [A]

Drain - Source Voltage : -V_{DS} [V]

Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width

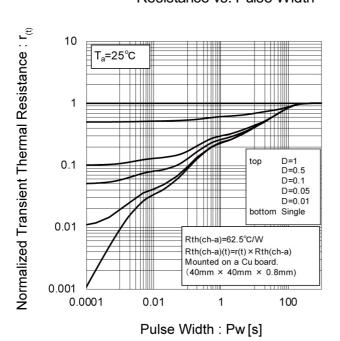
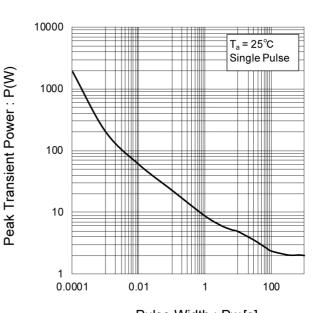


Fig.4 Single Pulse Maximum Power dissipation



Pulse Width: Pw[s]

Fig.5 Typical Output Characteristics(I)

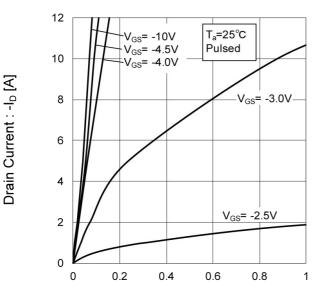
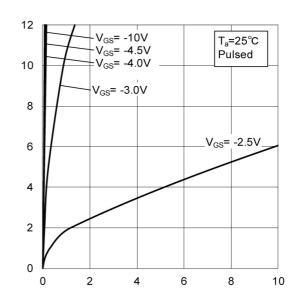


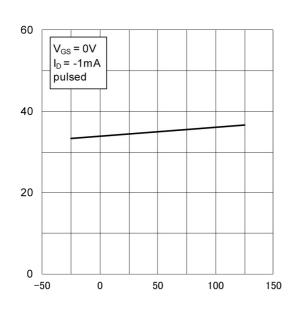
Fig.6 Typical Output Characteristics(II)



Drain Current : -I_D [A]

Drain - Source Voltage : -V_{DS} [V]

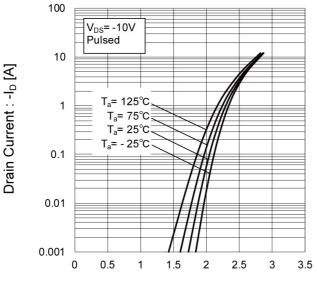
Fig.7 Breakdown Voltage vs. Junction Temperature



Junction Temperature : T_i [°C]

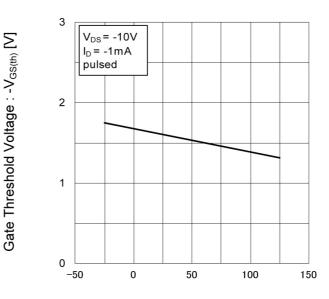
Drain-Source Breakdown Voltage: -V_{(BR)DSS} [V]

Fig.8 Typical Transfer Characteristics



Gate - Source Voltage : -V_{GS} [V]

Fig.9 Gate Threshold Voltage vs. Junction Temperature



Junction Temperature : T_j [°C]

Fig.10 Tranceconductance vs. Drain Current

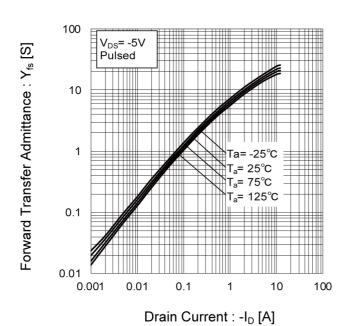


Fig.11 Drain Current Derating Curve

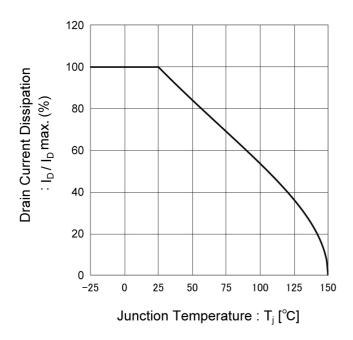
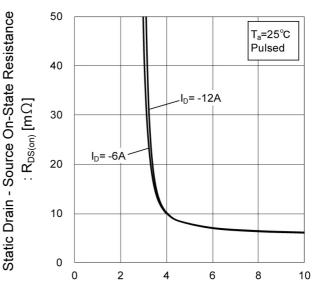


Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage



Gate - Source Voltage : -V_{GS} [V]

Fig.13 Static Drain - Source On - State Resistance vs. Junction Temperature

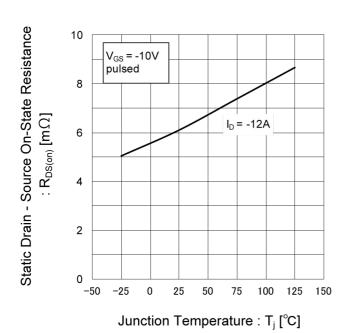


Fig.14 Static Drain - Source On - State Resistance vs. Drain Current(I)

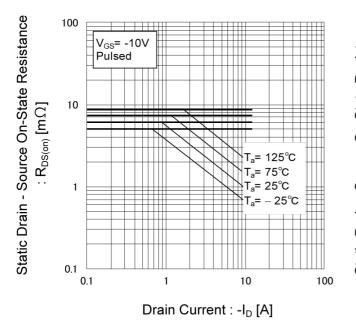


Fig.15 Static Drain - Source On - State Resistance vs. Drain Current(II)

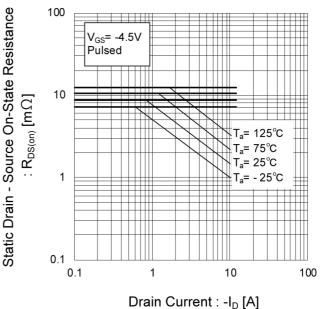


Fig.16 Typical Capacitance vs. Drain - Source Voltage

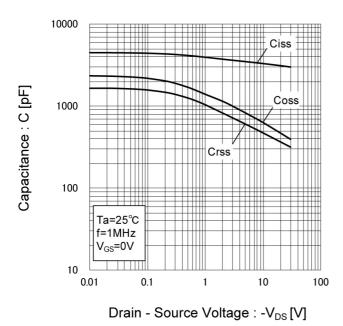
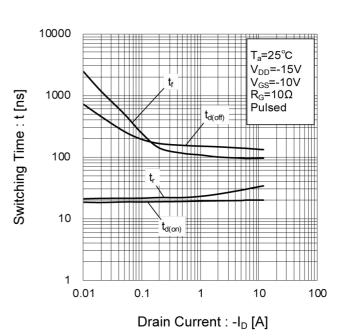


Fig.17 Switching Characteristics



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Fig.18 Dynamic Input Characteristics

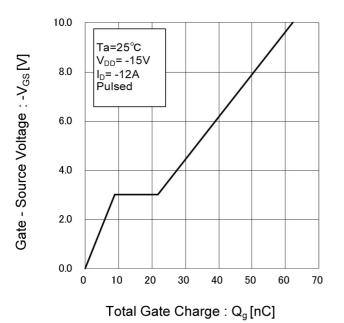
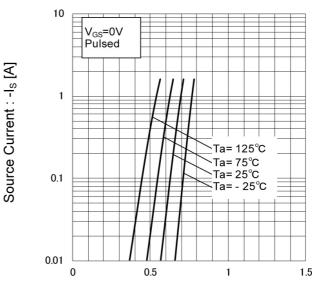


Fig.19 Source Current vs. Source Drain Voltage



Source - Drain Voltage : -V_{SD} [V]

Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

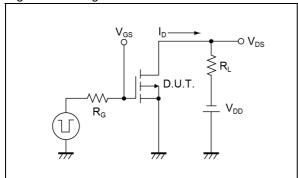


Fig.2-1 Gate Charge Measurement Circuit

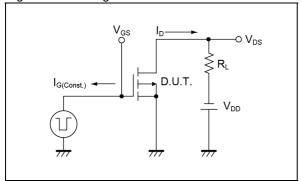


Fig.1-2 Switching Waveforms

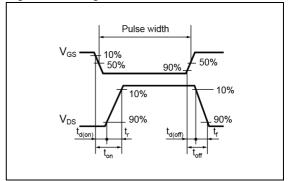
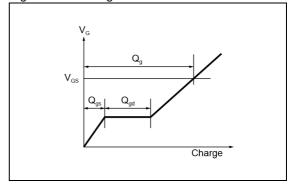


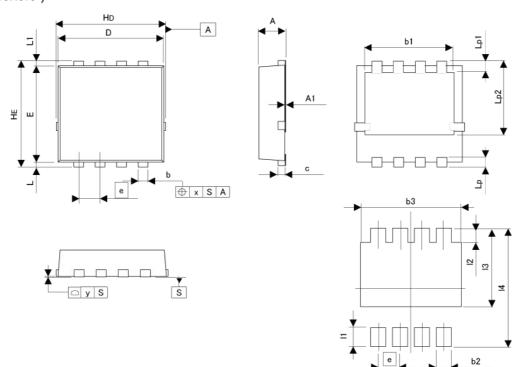
Fig.2-2 Gate Charge Waveform



Dimensions

HSMT8

(3.3x3.3)



Pattern of terminal position areas [Not a pattern of soldering pads]

DIM	MILIME	TERS	INC	HES
DIIVI	MIN	MAX	MIN	MAX
Α	0.70	0.90	0.028	0.035
A1	0.00	0.05	0.000	0.002
b	0.27	0.37	0.011	0.015
b1	2.50	2.70	0.098	0.106
С	0.10	0.30	0.004	0.012
D	3.10	3.30	0.122	0.130
E	2.90	3.10	0.114	0.122
е	0.	65	0.0)26
HD	3.20	3.40	0.126	0.134
HE	3.20	3.40	0.126	0.134
L	0.07	0.25	0.003	0.010
L1	0.07	0.25	0.003	0.010
Lp	0.20	0.40	0.008	0.016
Lp1	0.25	0.45	0.010	0.018
Lp2	2.20	2.40	0.087	0.094
Х	-	0.10	-	0.004
У	- 1	0.10	-	0.004

DIM	MILIME	ETERS	INC	HES
DIIVI	MIN	MAX	MIN	MAX
b2	101	0.47	u u	0.019
b3	1.5	2.70	-	0.106
I1	-	0.50	-	0.020
12	-	0.55	-	0.022
13	9. 5 .3	2.40	-	0.094
14	121	3.40	-	0.134

Dimension in mm/inches



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